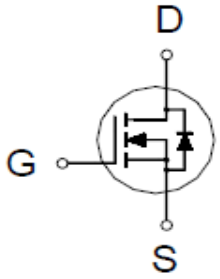
PE636BA

N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	9mΩ @V_{GS} = 10V	33A

PDFN 3X3P



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current[3]	T_c = 25 °C	I_D	33	A
	T_c = 100 °C		21	
	T_A = 25 °C		10	
	T_A= 70 °C		8	
Pulsed Drain Current[1]		I_{DM}	100	
Avalanche Current		I_{AS}	20	
Avalanche Energy	L =0.1mH	E_{AS}	20	mJ
Power Dissipation	T_C = 25 °C	P_D	17.8	W
	T_C = 100 °C		7	
	T_A = 25 °C		1.7	
	T_A = 70 °C		1	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	$R_{\theta JA}$		75	°C / W
Junction-to-Case	$R_{\theta JC}$		7	

[1]Pulse width limited by maximum junction temperature.

[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

[3]Package limitation current is 13A

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.3	1.8	2.3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V			1	μA
		V_{DS} = 20V, V_{GS} = 0V, T_J = 55 °C			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 10A		9.9	12	mΩ
		V_{GS} = 10V , I_D = 10A		7.4	9	
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 10A		34		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		774		pF
Output Capacitance	C_{oss}			139		
Reverse Transfer Capacitance	C_{rss}			81		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		3.1		Ω
Total Gate Charge[2]	Q_g(V_{GS}=10V)	V_{DS} = 15V , I_D = 10A		15.5		nC
	Q_g(V_{GS}=4.5V)			8.3		
Gate-Source Charge[2]	Q_{gs}			2.2		
Gate-Drain Charge[2]	Q_{gd}			4.4		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD}= 15V, I_D ≅ 10A, V_{GEN} = 10V, R_G= 6Ω		23		nS
Rise Time[2]	t_r			20		
Turn-Off Delay Time[2]	$t_{d(off)}$			40		
Fall Time[2]	t_f			20		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				14.8	A
Forward Voltage[1]	V_{SD}	I_F = 10A, V_{GS} = 0V			1.2	V
Reverse Recovery Time	t_{rr}	I_F = 10A, dI_F/dt = 100A / μS		9.5		nS
Reverse Recovery Charge	Q_{rr}			1.4		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

[3]Package limitation current is 13A.

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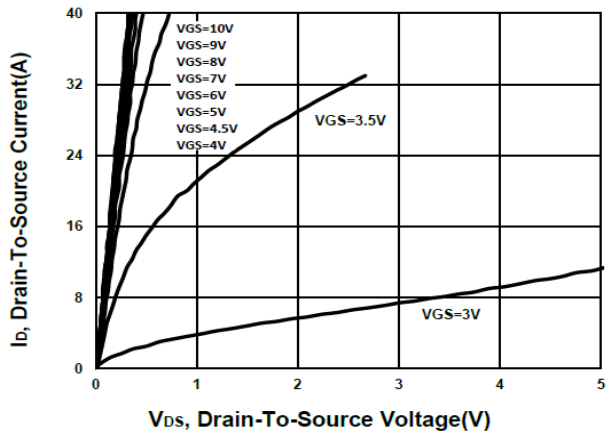
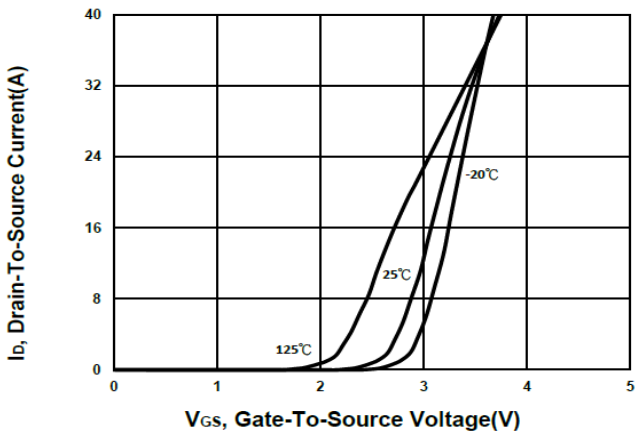
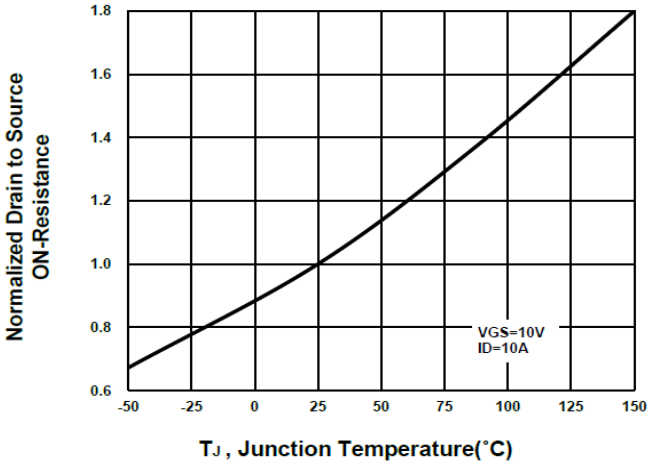
Output Characteristics



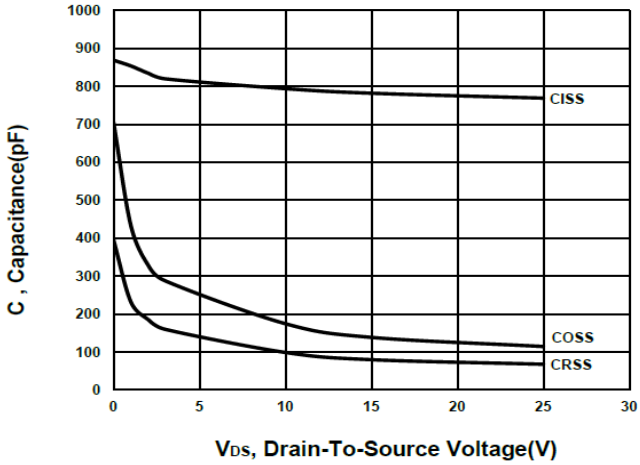
Transfer Characteristics



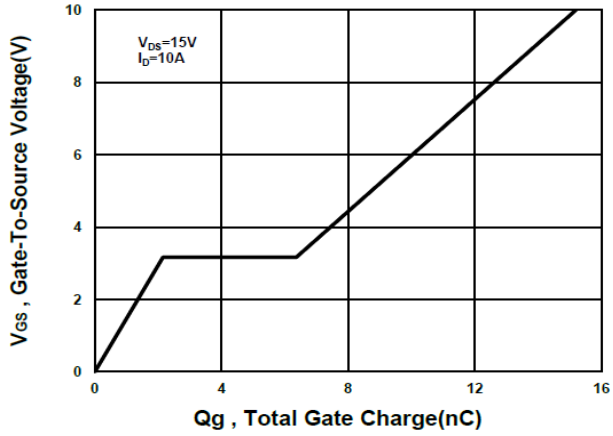
On-Resistance VS Temperature



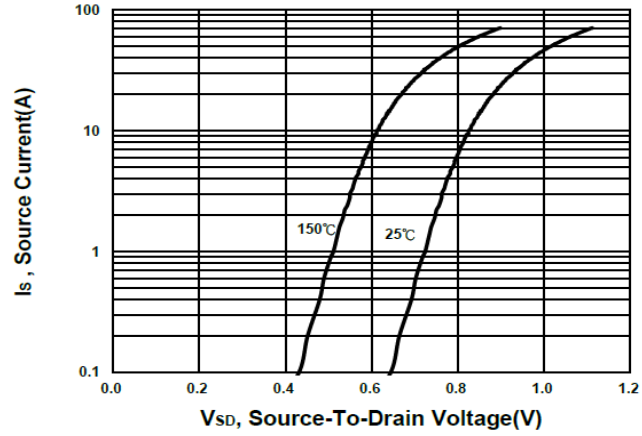
Capacitance Characteristic



Gate charge Characteristics



Source-Drain Diode Forward Voltage



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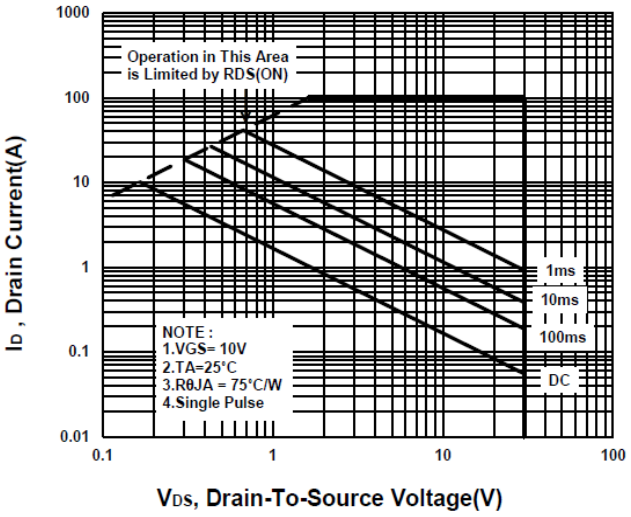
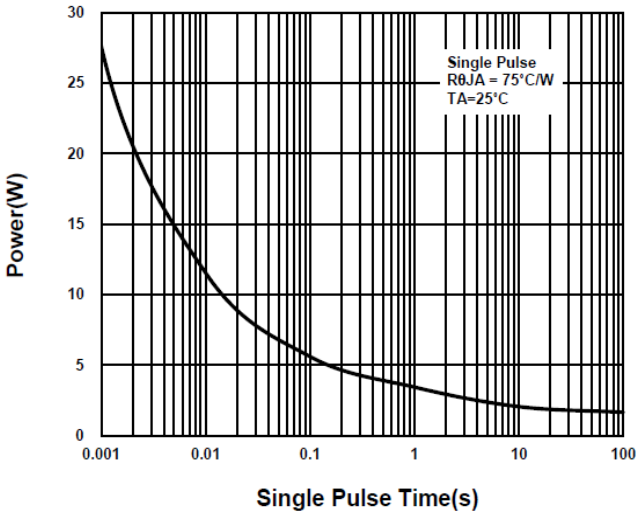
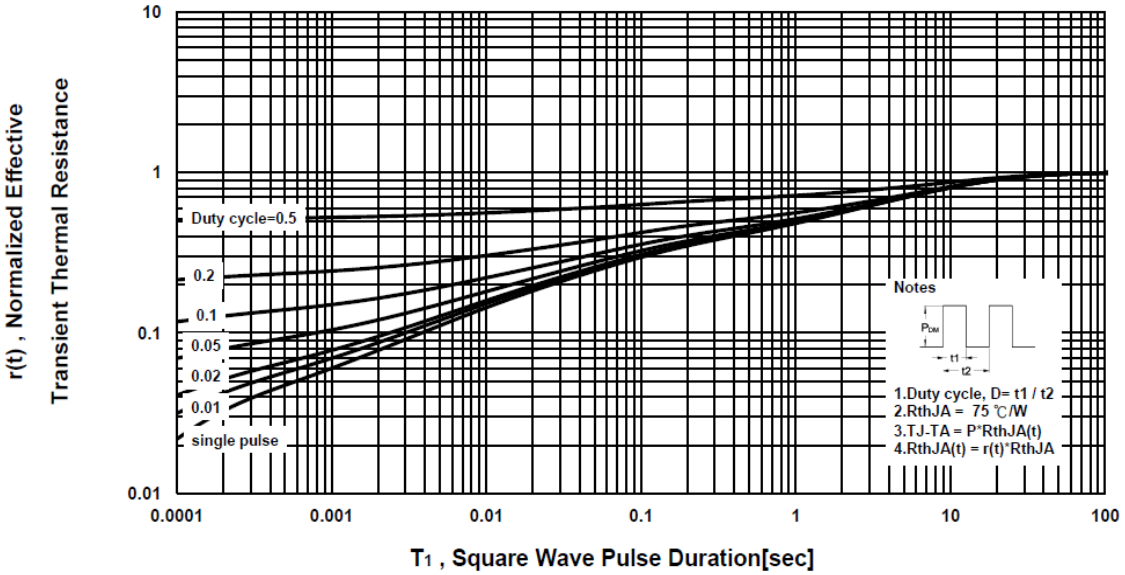
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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Package Dimension

PDFN 3x3P MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	3	3.3	3.6	I	0.65	0.8	0.9
B	2.88	3	3.2	J	0.1	0.15	0.25
C	2.9	3	3.25	K	0.59		
D	2.29	2.45	2.69	L	0°	10°	12°
E	3	3.3	3.6	M	0.14	0.3	0.4
F	0	0.1	0.2	N	0.55	0.65	0.75
G	1.35	1.75	2.2	O		0.2	
H	0.15	0.3	0.55	P	0		0.2